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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	180MHz
Connectivity	CANbus, EBI/EMI, I ² C, IrDA, LINbus, SAI, SD, SPDIF-Rx, SPI, UART/USART, USB, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I ² S, LVD, POR, PWM, WDT
Number of I/O	81
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	128K x 8
Voltage - Supply (Vcc/Vdd)	1.7V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f446vet6

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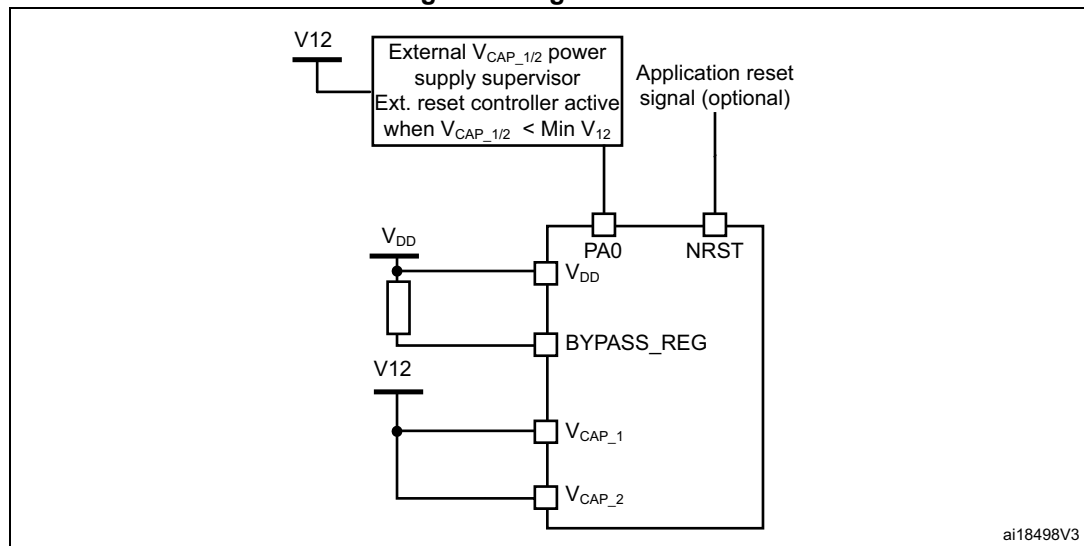
Since the internal voltage scaling is not managed internally, the external voltage value must be aligned with the targeted maximum frequency. The two 2.2 μF ceramic capacitors should be replaced by two 100 nF decoupling capacitors.

When the regulator is OFF, there is no more internal monitoring on V_{12} . An external power supply supervisor should be used to monitor the V_{12} of the logic power domain. PA0 pin should be used for this purpose, and act as power-on reset on V_{12} power domain.

In regulator OFF mode, the following features are no more supported:

- PA0 cannot be used as a GPIO pin since it allows to reset a part of the V_{12} logic power domain which is not reset by the NRST pin.
- As long as PA0 is kept low, the debug mode cannot be used under power-on reset. As a consequence, PA0 and NRST pins must be managed separately if the debug connection under reset or pre-reset is required.
- The over-drive and under-drive modes are not available.

Figure 7. Regulator OFF



The following conditions must be respected:

- V_{DD} should always be higher than V_{CAP_1} and V_{CAP_2} to avoid current injection between power domains.
- If the time for V_{CAP_1} and V_{CAP_2} to reach V_{12} minimum value is faster than the time for V_{DD} to reach 1.7 V, then PA0 should be kept low to cover both conditions: until V_{CAP_1} and V_{CAP_2} reach V_{12} minimum value and until V_{DD} reaches 1.7 V (see [Figure 8](#)).
- Otherwise, if the time for V_{CAP_1} and V_{CAP_2} to reach V_{12} minimum value is slower than the time for V_{DD} to reach 1.7 V, then PA0 could be asserted low externally (see [Figure 9](#)).
- If V_{CAP_1} and V_{CAP_2} go below V_{12} minimum value and V_{DD} is higher than 1.7 V, then a reset must be asserted on PA0 pin.

Note: The minimum value of V_{12} depends on the maximum frequency targeted in the application.

Table 4. Regulator ON/OFF and internal reset ON/OFF availability

Package	Regulator ON	Regulator OFF	Internal reset ON	Internal reset OFF
LQFP144	Yes	No	Yes PDR_ON set to V _{DD}	Yes PDR_ON set to V _{SS}
UFBGA144	Yes BYPASS_REG set to V _{ss}	Yes BYPASS_REG set to V _{DD}		
WLCSP81				

3.18 Real-time clock (RTC), backup SRAM and backup registers

The backup domain includes:

- The real-time clock (RTC)
- 4 Kbytes of backup SRAM
- 20 backup registers

The real-time clock (RTC) is an independent BCD timer/counter. Dedicated registers contain the second, minute, hour (in 12/24 hour), week day, date, month, year, in BCD (binary-coded decimal) format. Correction for 28, 29 (leap year), 30, and 31 day of the month are performed automatically. The RTC provides a programmable alarm and programmable periodic interrupts with wakeup from Stop and Standby modes. The sub-seconds value is also available in binary format.

It is clocked by a 32.768 kHz external crystal, resonator or oscillator, the internal low-power RC oscillator or the high-speed external clock divided by 128. The internal low-speed RC has a typical frequency of 32 kHz. The RTC can be calibrated using an external 512 Hz output to compensate for any natural quartz deviation.

Two alarm registers are used to generate an alarm at a specific time and calendar fields can be independently masked for alarm comparison. To generate a periodic interrupt, a 16-bit programmable binary auto-reload downcounter with programmable resolution is available and allows automatic wakeup and periodic alarms from every 120 μ s to every 36 hours.

A 20-bit prescaler is used for the time base clock. It is by default configured to generate a time base of 1 second from a clock at 32.768 kHz.

The 4-Kbyte backup SRAM is an EEPROM-like memory area. It can be used to store data which need to be retained in VBAT and standby mode. This memory area is disabled by default to minimize power consumption (see [Section 3.19: Low-power modes](#)). It can be enabled by software.

The backup registers are 32-bit registers used to store 80 bytes of user application data when V_{DD} power is not present. Backup registers are not reset by a system, a power reset, or when the device wakes up from the Standby mode (see [Section 3.19: Low-power modes](#)).

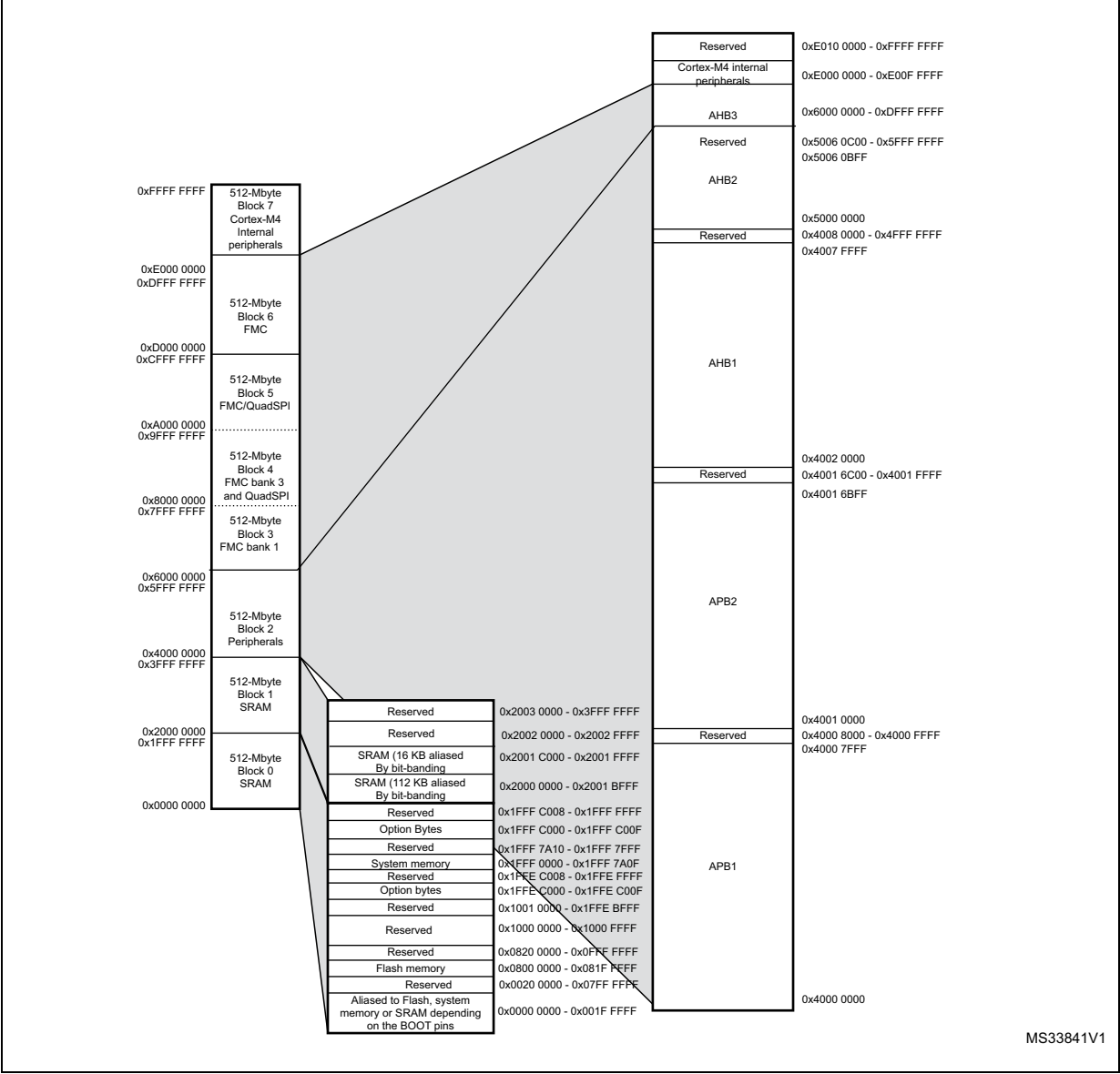
Additional 32-bit registers contain the programmable alarm subseconds, seconds, minutes, hours, day, and date.

Like backup SRAM, the RTC and backup registers are supplied through a switch that is powered either from the V_{DD} supply when present or from the V_{BAT} pin.

5 Memory mapping

The memory map is shown in [Figure 15](#)

Figure 15. Memory map



MS33841V1

Table 14. Current characteristics

Symbol	Ratings	Max.	Unit
ΣI_{VDD}	Total current into sum of all V_{DD} power lines (source) ⁽¹⁾	240	mA
ΣI_{VSS}	Total current out of sum of all V_{SS} ground lines (sink) ⁽¹⁾	- 240	
ΣI_{VDDUSB}	Total current into V_{DDUSB} power line (source)	25	
I_{VDD}	Maximum current into each V_{DD} power pin (source) ⁽¹⁾	100	
I_{VSS}	Maximum current out of each V_{SS} ground pin (sink) ⁽¹⁾	- 100	
I_{IO}	Output current sunk by any I/O and control pin	25	
	Output current sourced by any I/Os and control pin	- 25	
ΣI_{IO}	Total output current sunk by sum of all I/Os and control pins ⁽²⁾	120	
	Total output current sunk by sum of all USB I/Os	25	
	Total output current sourced by sum of all I/Os and control pins ⁽²⁾	-120	
$I_{INJ(PIN)}$	Injected current on FT, FTf, RST and B pins	-5/+0 ⁽³⁾	
	Injected current on TTa pins	±5 ⁽⁴⁾	
$\Sigma I_{INJ(PIN)}$	Total injected current (sum of all I/O and control pins) ⁽⁵⁾	±25	

1. All main power (V_{DD} , V_{DDA}) and ground (V_{SS} , V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
2. This current consumption must be correctly distributed over all I/Os and control pins. The total output current must not be sunk/sourced between two consecutive power supply pins referring to high pin count LQFP packages.
3. Positive injection is not possible on these I/Os and does not occur for input voltages lower than the specified maximum value.
4. A positive injection is induced by $V_{IN} > V_{DDA}$ while a negative injection is induced by $V_{IN} < V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer to [Table 13](#) for the maximum allowed input voltage value.
5. When several inputs are submitted to a current injection, the maximum $\Sigma I_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values).

Table 15. Thermal characteristics

Symbol	Ratings	Value	Unit
T_{STG}	Storage temperature range	-65 to +150	°C
T_J	Maximum junction temperature	125	°C

Table 34. Switching output I/O current consumption⁽¹⁾ (continued)

Symbol	Parameter	Conditions	I/O toggling frequency (fsw)	Typ	Unit
I _{DDIO}	I/O switching Current	V _{DD} = 3.3 V C _{EXT} = 10 pF C = C _{INT} + C _{EXT} + C _S	2 MHz	0.18	mA
			8 MHz	0.67	
			25 MHz	2.09	
			50 MHz	3.6	
			60 MHz	4.5	
			84 MHz	7.8	
			90 MHz	9.8	
		V _{DD} = 3.3 V C _{EXT} = 22 pF C = C _{INT} + C _{EXT} + C _S	2 MHz	0.26	
			8 MHz	1.01	
			25 MHz	3.14	
			50 MHz	6.39	
			60 MHz	10.68	
		V _{DD} = 3.3 V C _{EXT} = 33 pF C = C _{INT} + C _{EXT} + C _S	2 MHz	0.33	
			8 MHz	1.29	
			25 MHz	4.23	
			50 MHz	11.02	

1. C_S is the PCB board capacitance including the pad pin. C_S = 7 pF (estimated value).

2. This test is performed by cutting the LQFP144 package pin (pad removal).

On-chip peripheral current consumption

The MCU is placed under the following conditions:

- At startup, all I/O pins are in analog input configuration.
- All peripherals are disabled unless otherwise mentioned.
- HCLK is the system clock. f_{PCLK1} = f_{HCLK}/4, and f_{PCLK2} = f_{HCLK}/2.

The given value is calculated by measuring the difference of current consumption

- with all peripherals clocked off
- with only one peripheral clocked on
- f_{HCLK} = 180 MHz (Scale1 + over-drive ON), f_{HCLK} = 144 MHz (Scale 2), f_{HCLK} = 120 MHz (Scale 3)"
- Ambient operating temperature is 25 °C and V_{DD}=3.3 V.

These tests are compliant with EIA/JESD 78A IC latchup standard.

Table 54. Electrical sensitivities

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	$T_A = +105\text{ }^{\circ}\text{C}$ conforming to JESD78A	II level A

6.3.16 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DD} (for standard, 3 V-capable I/O pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibility to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (>5 LSB TUE), out of conventional limits of induced leakage current on adjacent pins (out of $-5\text{ }\mu\text{A}/+0\text{ }\mu\text{A}$ range), or other functional failure (for example reset, oscillator frequency deviation).

Negative induced leakage current is caused by negative injection and positive induced leakage current by positive injection.

The test results are given in [Table 55](#).

Table 55. I/O current injection susceptibility⁽¹⁾

Symbol	Description	Functional susceptibility		Unit
		Negative injection	Positive injection	
I_{INJ}	Injected current on BOOT0 pin	-0	NA	mA
	Injected current on NRST pin	-0	NA	
	Injected current on PE2, PE3, PE4, PE5, PE6, PC13, PC14, PF10, PH0, PH1, NRST, PC0, PC1, PC2, PC3, PG15, PB3, PB4, PB5, PB6, PB7, PB8, PB9, PE0, PE1	-0	NA	
	Injected current on any other FT and FTf pins	-5	NA	
	Injected current on any other pins	-5	+5	

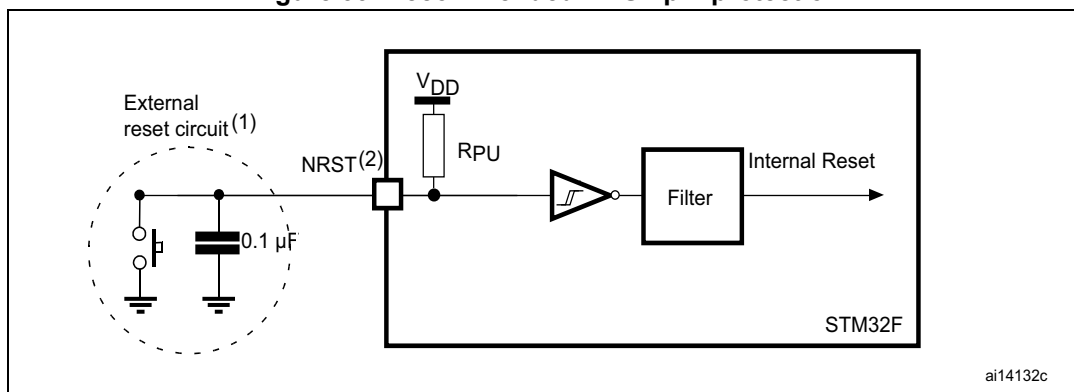
1. NA = not applicable.

Note: *It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.*

Table 58. I/O AC characteristics⁽¹⁾⁽²⁾ (continued)

OSPEEDR y[1:0] bit value ⁽¹⁾	Symbol	Parameter	Conditions	Min	Typ	Max	Unit
01	$f_{\max(\text{IO})\text{out}}$	Maximum frequency ⁽³⁾	$C_L = 50 \text{ pF}, V_{DD} \geq 2.7 \text{ V}$	-	-	25	MHz
			$C_L = 50 \text{ pF}, V_{DD} \geq 1.8 \text{ V}$	-	-	12.5	
			$C_L = 50 \text{ pF}, V_{DD} \geq 1.7 \text{ V}$	-	-	10	
			$C_L = 10 \text{ pF}, V_{DD} \geq 2.7 \text{ V}$	-	-	50	
			$C_L = 10 \text{ pF}, V_{DD} \geq 1.8 \text{ V}$	-	-	20	
			$C_L = 10 \text{ pF}, V_{DD} \geq 1.7 \text{ V}$	-	-	12.5	
	$t_{f(\text{IO})\text{out}}/$ $t_{r(\text{IO})\text{out}}$	Output high to low level fall time and output low to high level rise time	$C_L = 50 \text{ pF}, V_{DD} \geq 2.7 \text{ V}$	-	-	10	ns
			$C_L = 10 \text{ pF}, V_{DD} \geq 2.7 \text{ V}$	-	-	6	
			$C_L = 50 \text{ pF}, V_{DD} \geq 1.7 \text{ V}$	-	-	20	
			$C_L = 10 \text{ pF}, V_{DD} \geq 1.7 \text{ V}$	-	-	10	
10	$f_{\max(\text{IO})\text{out}}$	Maximum frequency ⁽³⁾	$C_L = 40 \text{ pF}, V_{DD} \geq 2.7 \text{ V}$	-	-	50 ⁽⁴⁾	MHz
			$C_L = 10 \text{ pF}, V_{DD} \geq 2.7 \text{ V}$	-	-	100 ⁽⁴⁾	
			$C_L = 40 \text{ pF}, V_{DD} \geq 1.7 \text{ V}$	-	-	25	
			$C_L = 10 \text{ pF}, V_{DD} \geq 1.8 \text{ V}$	-	-	50	
			$C_L = 10 \text{ pF}, V_{DD} \geq 1.7 \text{ V}$	-	-	42.5	
	$t_{f(\text{IO})\text{out}}/$ $t_{r(\text{IO})\text{out}}$	Output high to low level fall time and output low to high level rise time	$C_L = 40 \text{ pF}, V_{DD} \geq 2.7 \text{ V}$	-	-	6	ns
			$C_L = 10 \text{ pF}, V_{DD} \geq 2.7 \text{ V}$	-	-	4	
			$C_L = 40 \text{ pF}, V_{DD} \geq 1.7 \text{ V}$	-	-	10	
			$C_L = 10 \text{ pF}, V_{DD} \geq 1.7 \text{ V}$	-	-	6	
11	$f_{\max(\text{IO})\text{out}}$	Maximum frequency ⁽³⁾	$C_L = 30 \text{ pF}, V_{DD} \geq 2.7 \text{ V}$	-	-	100 ⁽⁴⁾	MHz
			$C_L = 30 \text{ pF}, V_{DD} \geq 1.8 \text{ V}$	-	-	50	
			$C_L = 30 \text{ pF}, V_{DD} \geq 1.7 \text{ V}$	-	-	42.5	
			$C_L = 10 \text{ pF}, V_{DD} \geq 2.7 \text{ V}$	-	-	180 ⁽⁴⁾	
			$C_L = 10 \text{ pF}, V_{DD} \geq 1.8 \text{ V}$	-	-	100	
			$C_L = 10 \text{ pF}, V_{DD} \geq 1.7 \text{ V}$	-	-	72.5	
	$t_{f(\text{IO})\text{out}}/$ $t_{r(\text{IO})\text{out}}$	Output high to low level fall time and output low to high level rise time	$C_L = 30 \text{ pF}, V_{DD} \geq 2.7 \text{ V}$	-	-	4	ns
			$C_L = 30 \text{ pF}, V_{DD} \geq 1.8 \text{ V}$	-	-	6	
			$C_L = 30 \text{ pF}, V_{DD} \geq 1.7 \text{ V}$	-	-	7	
			$C_L = 10 \text{ pF}, V_{DD} \geq 2.7 \text{ V}$	-	-	2.5	
			$C_L = 10 \text{ pF}, V_{DD} \geq 1.8 \text{ V}$	-	-	3.5	
			$C_L = 10 \text{ pF}, V_{DD} \geq 1.7 \text{ V}$	-	-	4	
-	$t_{\text{EXTI}pw}$	Pulse width of external signals detected by the EXTI controller	-	10	-	-	ns

Figure 33. Recommended NRST pin protection



1. The reset network protects the device against parasitic resets.
2. The user must ensure that the level on the NRST pin can go below the $V_{IL(NRST)}$ max level specified in [Table 59](#). Otherwise the reset is not taken into account by the device.
3. The external capacitor on NRST must be placed as close as possible to the device.

6.3.19 TIM timer characteristics

The parameters given in [Table 60](#) are guaranteed by design.

Refer to [Section 6.3.17: I/O port characteristics](#) for details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output).

Table 60. TIMx characteristics⁽¹⁾⁽²⁾

Symbol	Parameter	Conditions ⁽³⁾	Min	Max	Unit
$t_{res(TIM)}$	Timer resolution time	AHB/APBx prescaler=1 or 2 or 4, $f_{TIMxCLK} = 180\text{ MHz}$	1	-	$t_{TIMxCLK}$
		AHB/APBx prescaler>4, $f_{TIMxCLK} = 90\text{ MHz}$	1	-	$t_{TIMxCLK}$
f_{EXT}	Timer external clock frequency on CH1 to CH4	$f_{TIMxCLK} = 180\text{ MHz}$	0	$f_{TIMxCLK}/2$	MHz
Res_{TIM}	Timer resolution		-	16/32	bit
t_{MAX_COUNT}	Maximum possible count with 32-bit counter	-	-	65536×65536	$t_{TIMxCLK}$

1. TIMx is used as a general term to refer to the TIM1 to TIM12 timers.
2. Guaranteed by design.
3. The maximum timer frequency on APB1 or APB2 is up to 180 MHz, by setting the TIMPRE bit in the RCC_DCKCFGR register, if APBx prescaler is 1 or 2 or 4, then $TIMxCLK = HCLK$, otherwise $TIMxCLK = 4 \times PCLKx$.

6.3.20 Communications interfaces

I²C interface characteristics

The I²C interface meets the requirements of the standard I²C communication protocol with the following restrictions: the I/O pins SDA and SCL too are mapped as not “true” open-drain. When configured as open-drain, the PMOS connected between the I/O pin and V_{DD} is disabled, but is still present.

Figure 35. FMPI²C timing diagram and measurement circuit

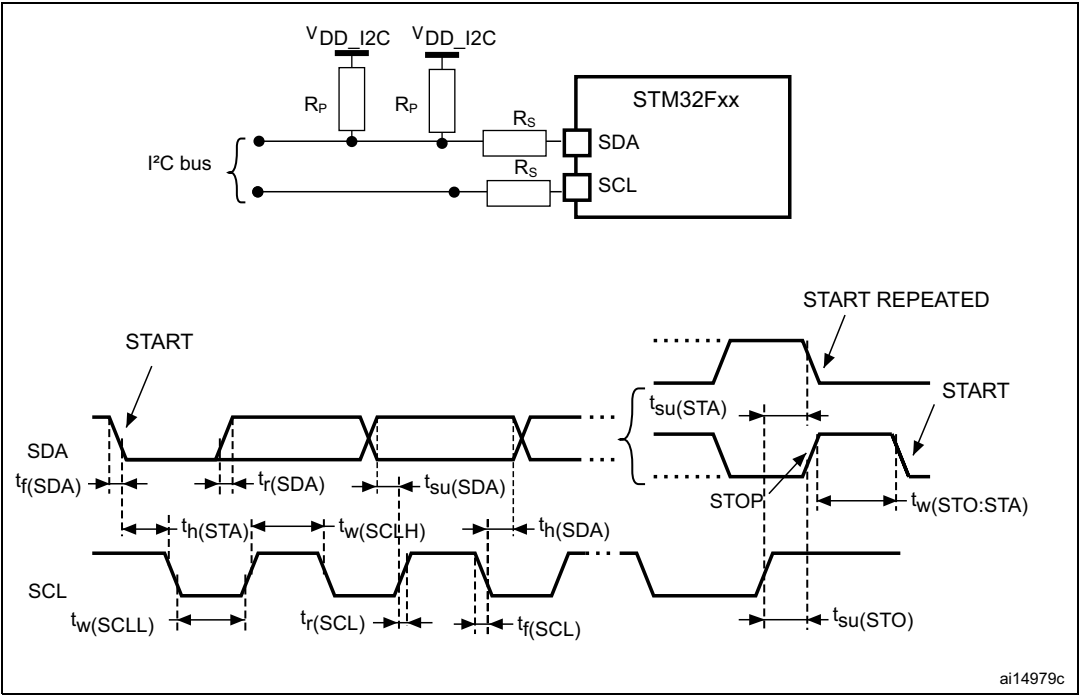


Table 63. SPI dynamic characteristics⁽¹⁾ (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{w(SCKH)}$	SCK high and low time	Master mode, SPI presc = 2	$T_{PCLK} - 1.5$	T_{PCLK}	$T_{PCLK} + 1.5$	ns
$t_{w(SCKL)}$						
$t_{su(NSS)}$	NSS setup time	Slave mode, SPI presc = 2	$4T_{PCLK}$	-	-	
$t_{h(NSS)}$	NSS hold time	Slave mode, SPI presc = 2	$2T_{PCLK}$	-	-	
$t_{su(MI)}$	Data input setup time	Master mode	4	-	-	
$t_{su(SI)}$		Slave mode	3	-	-	
$t_{h(MI)}$	Data input hold time	Master mode	4	-	-	
$t_{h(SI)}$		Slave mode	2	-	-	
$t_{a(SO)}$	Data output access time	Slave mode	7	-	21	
$t_{dis(SO)}$	Data output disable time	Slave mode	5	-	12	
$t_{v(SO)}$	Data output valid/hold time	Slave mode (after enable edge), $2.7V \leq V_{DD} \leq 3.6V$	-	7.5	22	
		Slave mode (after enable edge), $1.7V \leq V_{DD} \leq 3.6V$	-	7.5	10.5	
$t_{h(SO)}$	Data output valid/hold time	Slave mode (after enable edge)	5	-	-	
$t_{v(MO)}$	Data output valid time	Master mode (after enable edge)	-	1.5	5	
$t_{h(MO)}$	Data output hold time	Master mode (after enable edge)	0	-	-	

1. Guaranteed based on test during characterization.
2. Maximum frequency in Slave transmitter mode is determined by the sum of $t_{v(SO)}$ and $t_{su(MI)}$ which has to fit into SCK low or high phase preceding the SCK sampling edge. This value can be achieved when the SPI communicates with a master having $t_{su(MI)} = 0$ while Duty(SCK) = 50%.

Figure 36. SPI timing diagram - slave mode and CPHA = 0

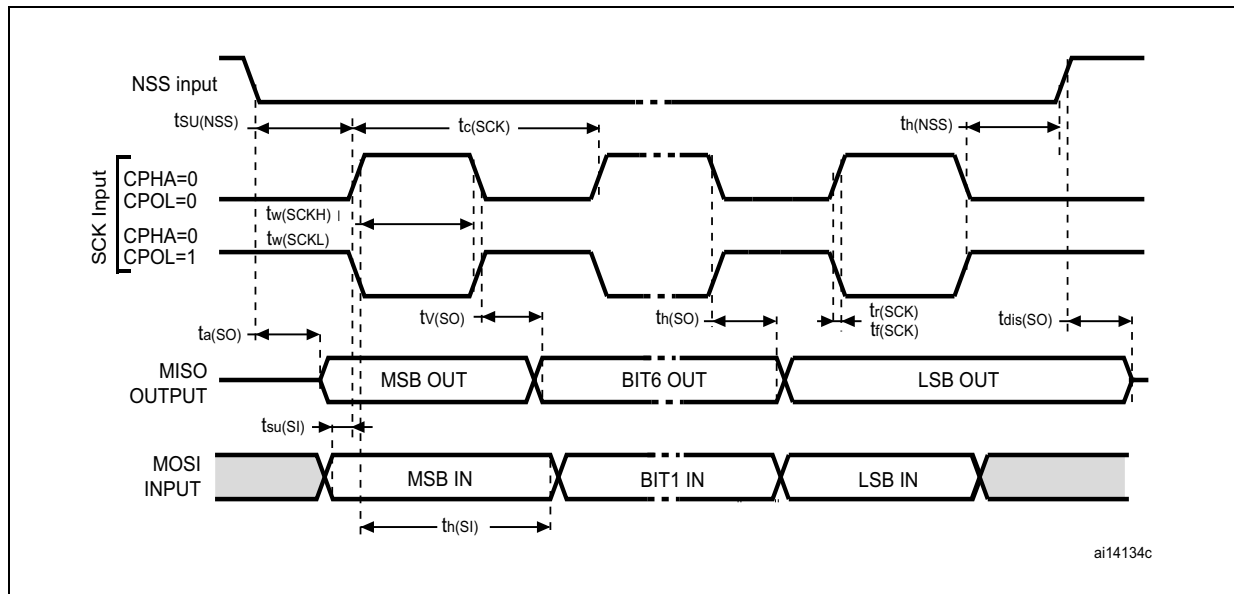


Table 66. I²S dynamic characteristics⁽¹⁾ (continued)

Symbol	Parameter	Conditions	Min	Max	Unit
$t_{v(WS)}$	WS valid time	Master mode	-	5.5	ns
$t_{h(WS)}$	WS hold time	Master mode	1	-	
$t_{su(WS)}$	WS setup time	Slave mode	1	-	
-		PCM short pulse Slave mode ⁽³⁾	2	-	
$t_{h(WS)}$	WS hold time	Slave mode	3	-	
-		PCM short pulse Slave mode ⁽³⁾	1.5	-	
$t_{su(SD_MR)}$	Data input setup time	Master receiver	3	-	
$t_{su(SD_SR)}$		Slave receiver	2.5	-	
$t_{h(SD_MR)}$	Data input hold time	Master receiver	4	-	
$t_{h(SD_SR)}$		Slave receiver	1	-	
$t_{v(SD_ST)}$	Data output valid time	Slave transmitter (after enable edge)	-	16	
$t_{v(SD_MT)}$		Master transmitter (after enable edge)	-	4.5	
$t_{h(SD_ST)}$	Data output hold time	Slave transmitter (after enable edge)	5	-	
$t_{h(SD_MT)}$		Master transmitter (after enable edge)	1	-	

1. Guaranteed based on test during characterization.
2. The maximum value of 256xFS is 45 MHz (APB1 maximum frequency).
3. Measurement done with respect to I2S_CK rising edge.

Note: Refer to the I2S section of RM0390 reference manual for more details on the sampling frequency (F_S).

f_{MCK} , f_{CK} , and D_{CK} values reflect only the digital peripheral behavior. The values of these parameters might be slightly impacted by the source clock precision. D_{CK} depends mainly on the value of ODD bit. The digital contribution leads to a minimum value of $(I2SDIV/(2*I2SDIV+ODD))$ and a maximum value of $(I2SDIV+ODD)/(2*I2SDIV+ODD)$. F_S maximum value is supported for each mode/condition.

Figure 41. SAI master timing waveforms

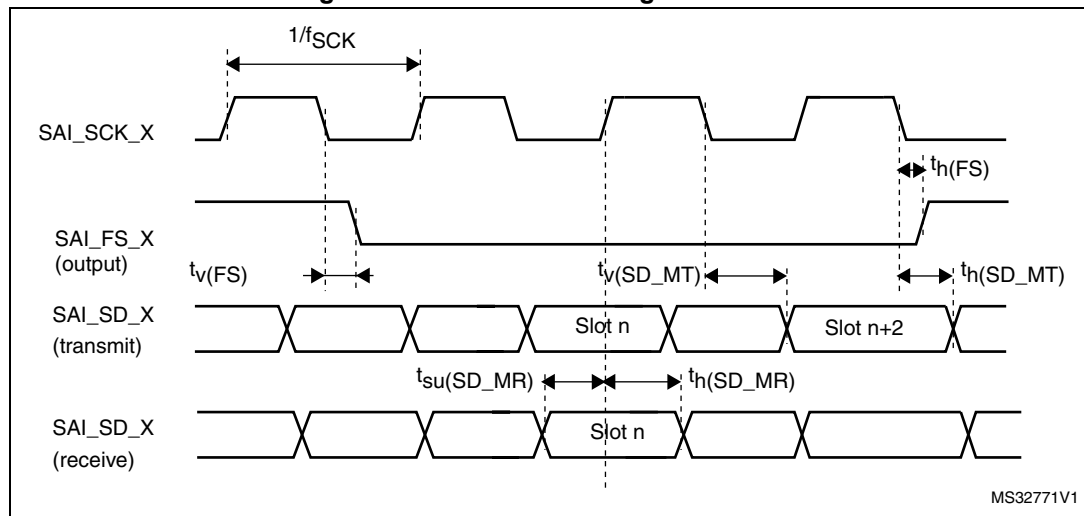
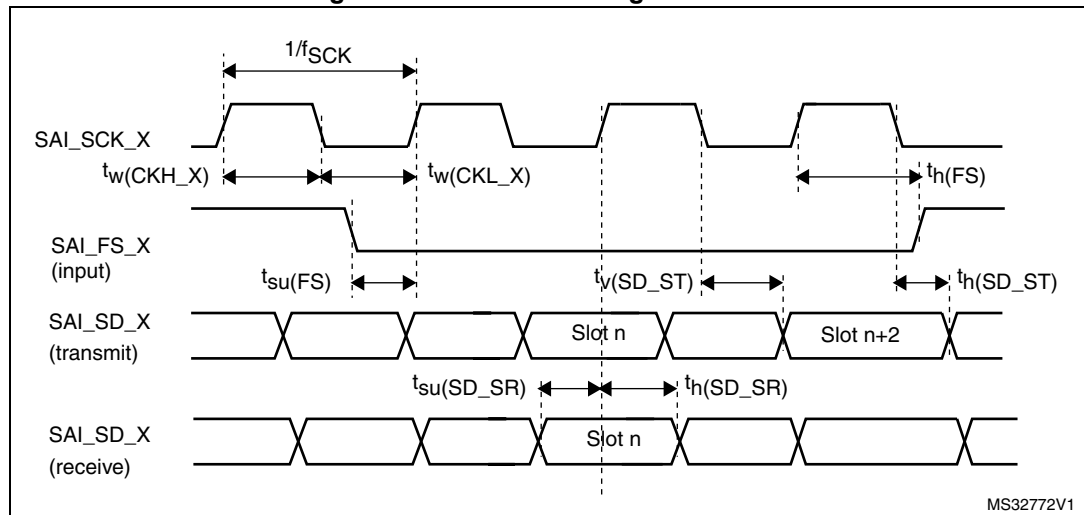


Figure 42. SAI slave timing waveforms



USB OTG full speed (FS) characteristics

This interface is present in both the USB OTG HS and USB OTG FS controllers.

Table 68. USB OTG full speed startup time

Symbol	Parameter	Max	Unit
$t_{\text{STARTUP}}^{(1)}$	USB OTG full speed transceiver startup time	1	μs

1. Guaranteed by design.

Figure 53. Asynchronous multiplexed PSRAM/NOR write waveforms

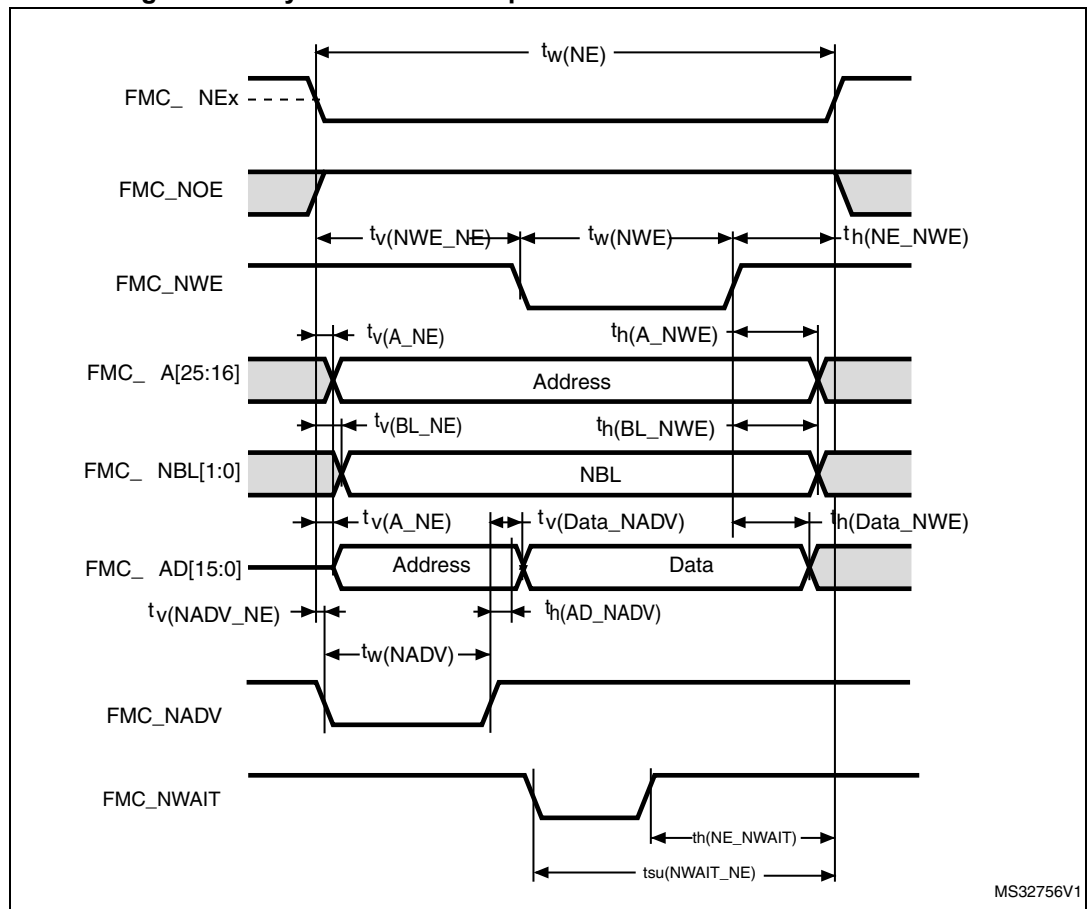


Table 103. LPDDR SDRAM write timings⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
$F_{(SDCLK)}$	Frequency of operation	-	84	MHz
$t_{w(SDCLK)}$	FMC_SDCLK period	$2T_{HCLK} - 0.5$	$2T_{HCLK} + 0.5$	ns
$t_{d(SDCLKL_Data)}$	Data output valid time	-	5	
$t_{h(SDCLKL_Data)}$	Data output hold time	0.5	-	
$t_{d(SDCLK_Add)}$	Address valid time	-	3	
$t_{d(SDCLKL_SDNWE)}$	SDNWE valid time	-	3	
$t_{h(SDCLKL_SDNWE)}$	SDNWE hold time	0	-	
$t_{d(SDCLKL_SDNE)}$	Chip select valid time	-	2.5	
$t_{h(SDCLKL_SDNE)}$	Chip select hold time	0	-	
$t_{d(SDCLKL_SDNRAS)}$	SDNRAS valid time	-	2	
$t_{h(SDCLKL_SDNRAS)}$	SDNRAS hold time	0	-	
$t_{d(SDCLKL_SDNCAS)}$	SDNCAS valid time	-	2	
$t_{d(SDCLKL_SDNCAS)}$	SDNCAS hold time	0	-	

1. CL = 10 pF.

2. Guaranteed based on test during characterization.

6.3.27 Camera interface (DCMI) timing specifications

Unless otherwise specified, the parameters given in [Table 104](#) for DCMI are derived from tests performed under the ambient temperature, f_{HCLK} frequency and V_{DD} supply voltage summarized in [Table 16](#), with the following configuration:

- DCMI_PIXCLK polarity: falling
- DCMI_VSYNC and DCMI_HSYNC polarity: high
- Data formats: 14 bits

Table 104. DCMI characteristics

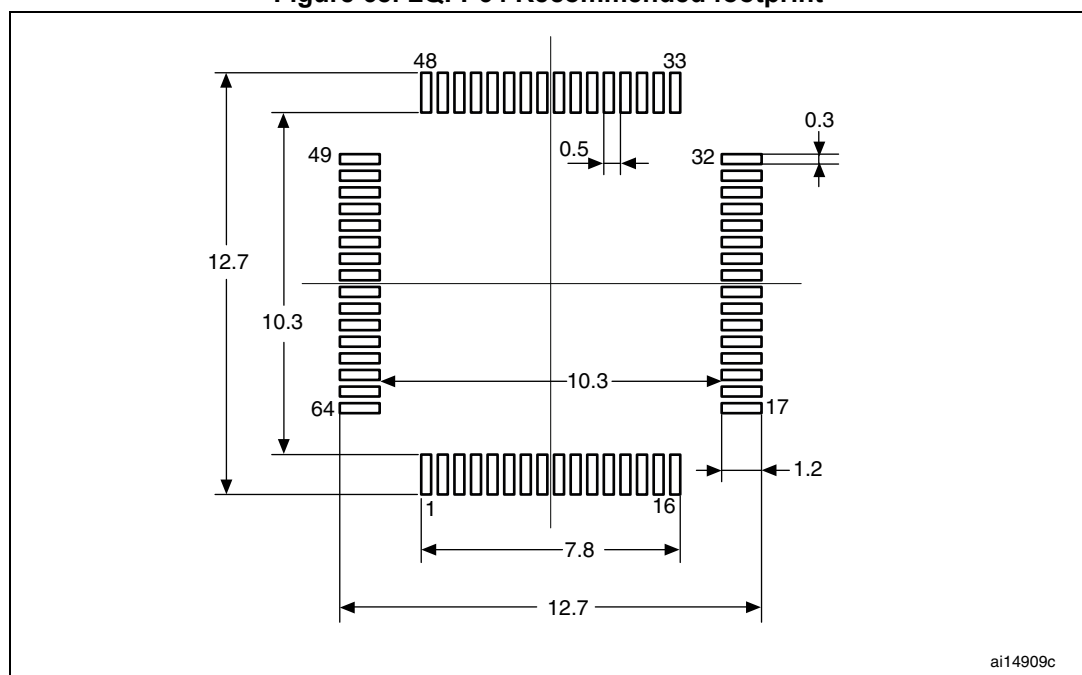
Symbol	Parameter	Min	Max	Unit
-	Frequency ratio DCMI_PIXCLK/ f_{HCLK}	-	0.4	-
DCMI_PIXCLK	Pixel clock input	-	54	MHz
D_{Pixel}	Pixel clock input duty cycle	30	70	%
$t_{su(DATA)}$	Data input setup time	1	-	ns
$t_{h(DATA)}$	Data input hold time	3.5	-	
$t_{su(HSYNC)}$ $t_{su(VSYNC)}$	DCMI_HSYNC/DCMI_VSYNC input setup time	2	-	
$t_{h(HSYNC)}$ $t_{h(VSYNC)}$	DCMI_HSYNC/DCMI_VSYNC input hold time	0	-	

Table 108. LQFP64 – 10 x 10 mm low-profile quad flat package mechanical data (continued)

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
D	11.800	12.000	12.200	0.4646	0.4724	0.4803
D1	9.800	10.000	10.200	0.3858	0.3937	0.4016
D3	-	7.500	-	-	0.2953	-
E	11.800	12.000	12.200	0.4646	0.4724	0.4803
E1	9.800	10.000	10.200	0.3858	0.3937	0.4016
E3	-	7.500	-	-	0.2953	-
e	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
K	0°	3.5°	7°	0°	3.5°	7°
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 68. LQFP64 Recommended footprint



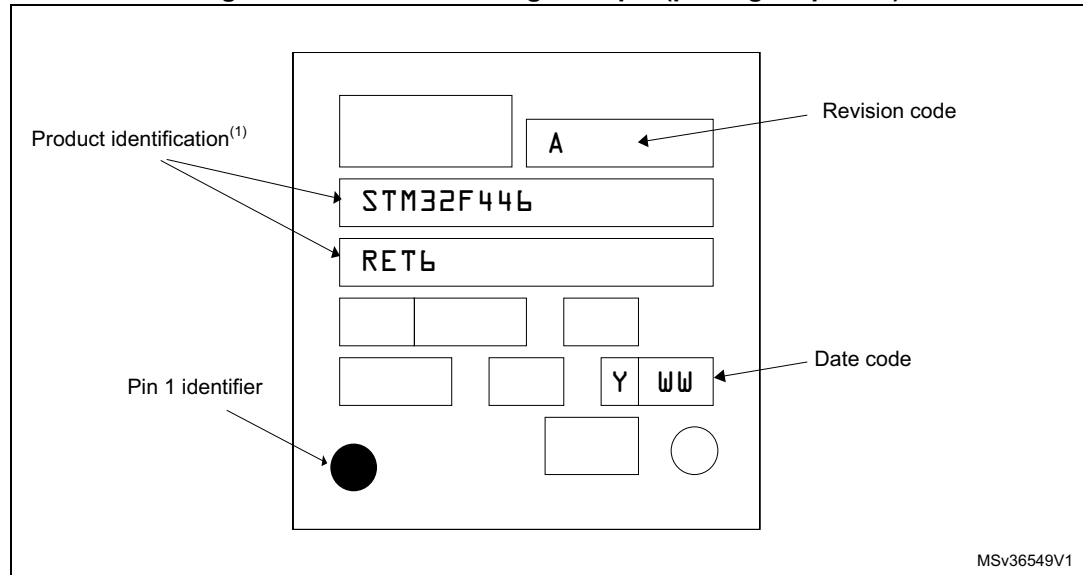
1. Drawing is not to scale.
2. Dimensions are in millimeters.

Device marking for LQFP64

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

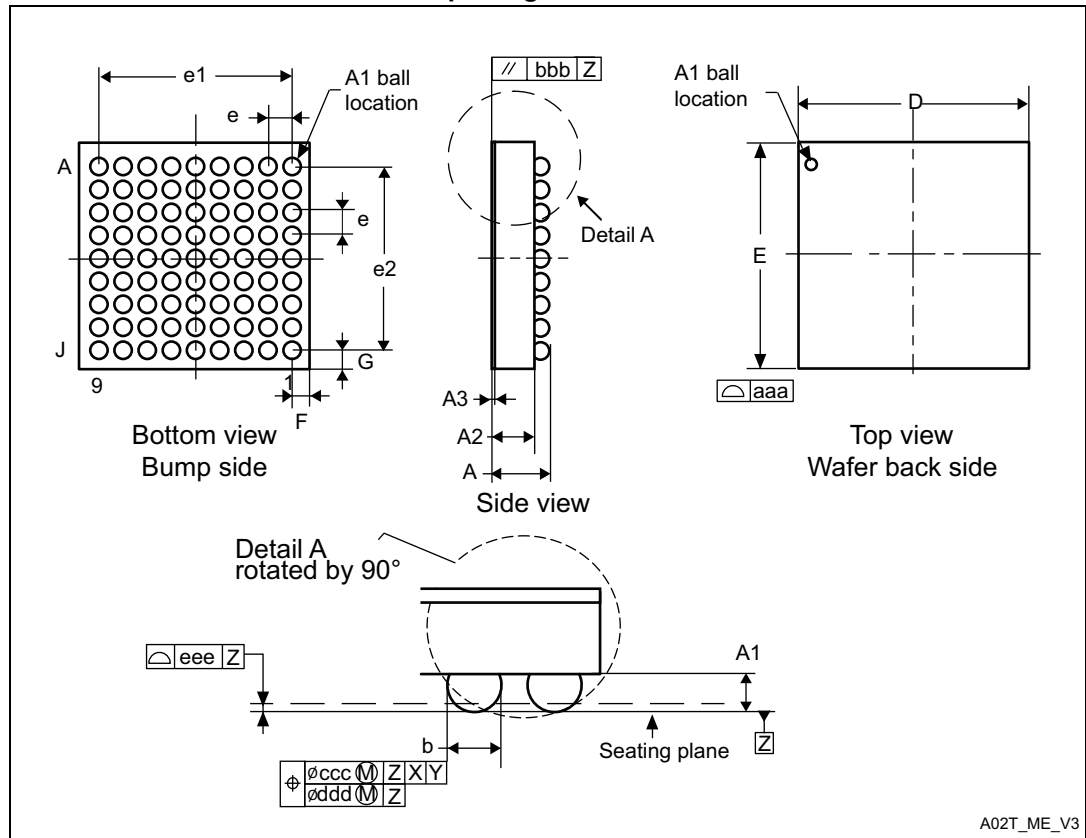
Figure 69. LQFP64 marking example (package top view)



1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

7.6 WLCSP81 package information

Figure 82. WLCSP81 - 81-pin, 3.693 x 3.815 mm, 0.4 mm pitch wafer level chip scale package outline



1. Drawing is not to scale.

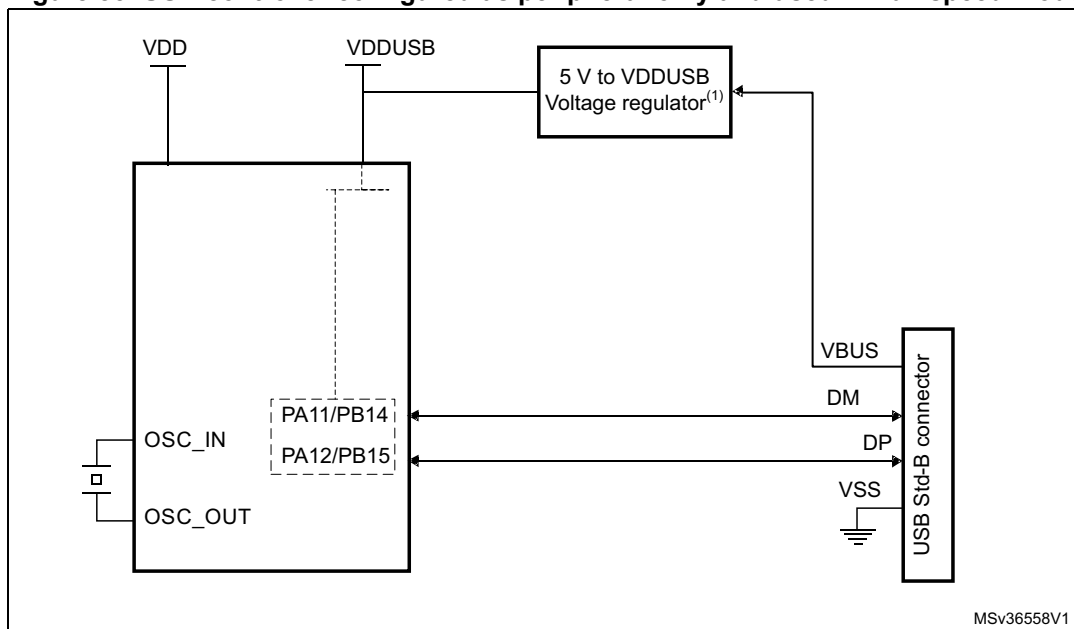
Table 115. WLCSP81- 81-pin, 3.693 x 3.815 mm, 0.4 mm pitch wafer level chip scale package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	-	-	0.600	-	-	0.0236
A1	-	0.170	-	-	0.0067	-
A2	-	0.380	-	-	0.0150	-
A3 ⁽²⁾	-	0.025	-	-	0.0010	-
b ⁽³⁾	0.220	0.250	0.280	0.0087	0.0098	0.0110
D	3.658	3.693	3.728	0.1440	0.1454	0.1468
E	3.780	3.815	3.850	0.1488	0.1502	0.1516
e	-	0.400	-	-	0.0157	-
e1	-	3.200	-	-	0.1260	-
e2	-	3.200	-	-	0.1260	-

Appendix A Application block diagrams

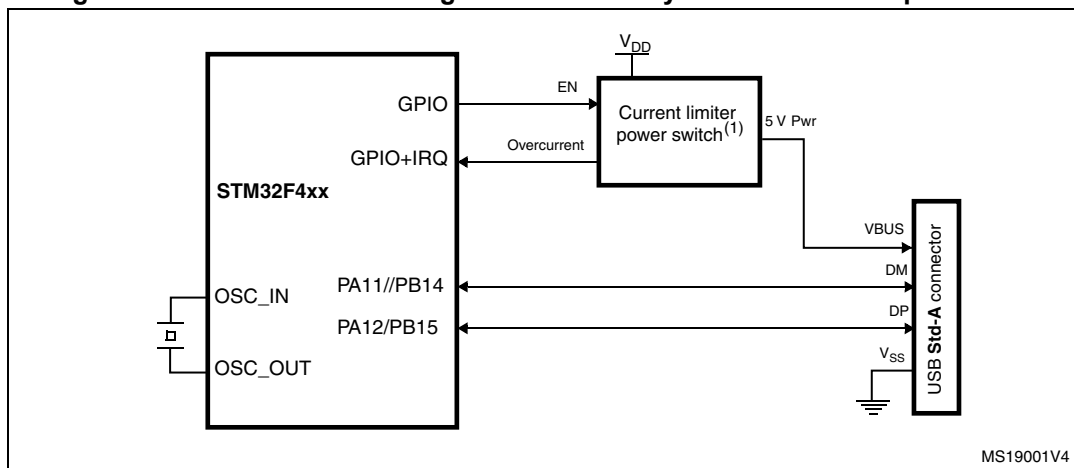
A.1 USB OTG full speed (FS) interface solutions

Figure 85. USB controller configured as peripheral-only and used in Full speed mode



1. External voltage regulator only needed when building a V_{BUS} powered device.
2. The same application can be developed using the OTG HS in FS mode to achieve enhanced performance thanks to the large Rx/Tx FIFO and to a dedicated DMA controller.

Figure 86. USB controller configured as host-only and used in full speed mode



1. The current limiter is required only if the application has to support a V_{BUS} powered device. A basic power switch can be used if 5 V are available on the application board.
2. The same application can be developed using the OTG HS in FS mode to achieve enhanced performance thanks to the large Rx/Tx FIFO and to a dedicated DMA controller.